

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:) CONFIRMATION NO.: 1732
Takanori MIMURA, et al.)
U.S. Serial No.: 10/647,433) Group Art Unit: 1765
Filed: August 26, 2003) Examiner: Binh X. Tran
For: SILICON ETCHING METHOD	

RESPONSE TO ELECTION REQUIREMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

A response to the Office Action mailed August 29, 2005 is due by September 29, 2005. The Action required election between the following:

Species A, with a SiO₂ film mask, and a RF power flux density at 6.8 to 12.5 W/cm²; and Species B, with a resist film, and a RF power flux density at 2.55 to 5.67 W/cm².

Applicants hereby elect <u>Species A</u> for examination in this application. Applicants advise that the elected species corresponds to all of claims 1-15 and 17-19. Applicants also advise that no change in the inventorship of the application would be required by cancellation of non-elected claim 16.

Applicants reserve the right to file divisional application(s) for any non-elected claims in due course.

IFW

U. S. Patent Application No. 10/647,433 Attorney Docket No. 033082M172 Page 2

It is submitted that this application now is in condition for examination on the merits and early action in that regard is solicited.

Respectfully submitted,

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